

S/N 08/902,133

PATENT

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7/11/2000
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: George C. Eckert II

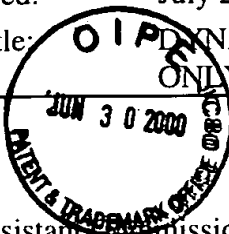
Serial No.: 08/902,133

Group Art Unit: 2815

Filed: July 29, 1997

Docket: 303.356US1

Title: **ADAPTIVE DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE**



AMENDMENT AND RESPONSE

Assistant Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action dated 28 March 2000. Please amend the application as follows:

IN THE SPECIFICATION

Please delete lines 6-18 of page 1 of the original specification, beginning with the heading "Cross Reference To Related Applications".

IN THE CLAIMS

Please amend the claims as follows:

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29. (Twice Amended) A memory cell comprising:
a storage electrode to store charge;
a control electrode[,] separated from [a] the storage electrode by an intergate dielectric;
and
wherein the intergate dielectric has a permittivity that is higher than a permittivity of silicon dioxide.

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66. (Amended) The memory device of claim 65 wherein:
the barrier energy between the floating gate and the insulator is less than approximately 2.0 eV;
the insulator comprises a material that has a larger electron affinity than silicon dioxide;
the floating gate comprises a material that has a smaller electron affinity than polycrystalline silicon; [and]

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01 FC:103
02 FC:102

108.00 OP

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